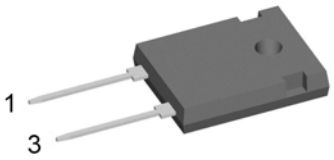
High Efficiency Standard Rectifier

V_{RRM}	=	1200V
I_{FAV}	=	60A
V_F	=	1.1V

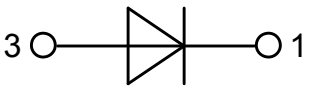
Single Diode

Part number

DLA60I1200HA



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

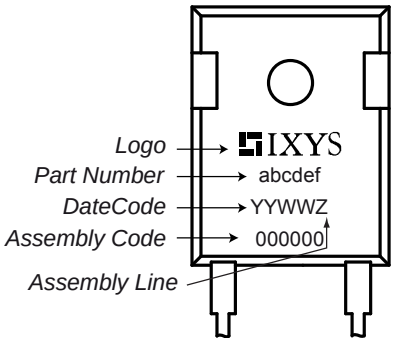
Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1300	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1200	V
I_R	*reverse current, drain current*	V_R = 1200 V	T_{VJ} = 25°C			30	µA
		V_R = 1200 V	T_{VJ} = 150°C			0.3	mA
V_F	*forward voltage drop*	I_F = 60 A	T_{VJ} = 25°C			1.19	V
		I_F = 120 A				1.42	V
		I_F = 60 A	T_{VJ} = 150 °C			1.10	V
		I_F = 120 A				1.41	V
I_{FAV}	*average forward current*	T_C = 150°C	T_{VJ} = 175°C			60	A
		rectangular d = 0.5					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 175°C			0.78	V
r_F	*slope resistance* }					5.1	mΩ
R_{thJC}	*thermal resistance junction to case*					0.3	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.25		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			500	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			850	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			920	A
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			725	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			780	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			3.62	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			3.52	kA²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			2.63	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			2.53	kA²s
C_J	*junction capacitance*	V_R = 400 V f = 1 MHz	T_{VJ} = 25°C		33		pF

Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal			70	A
T_{stg}	*storage temperature*		-55		150	°C
T_{VJ}	*virtual junction temperature*		-55		175	°C
Weight				6		g
M_D	*mounting torque*		0.8		1.2	Nm
F_C	*mounting force with clip*		20		120	N

Product Marking

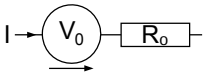


Part number

D = Diode
L = High Efficiency Standard Rectifier
A = (up to 1200V)
60 = Current Rating [A]
I = Single Diode
1200 = Reverse Voltage [V]
HA = TO-247AD (2)

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DLA60I1200HA	DLA60I1200HA	Tube	30	508170

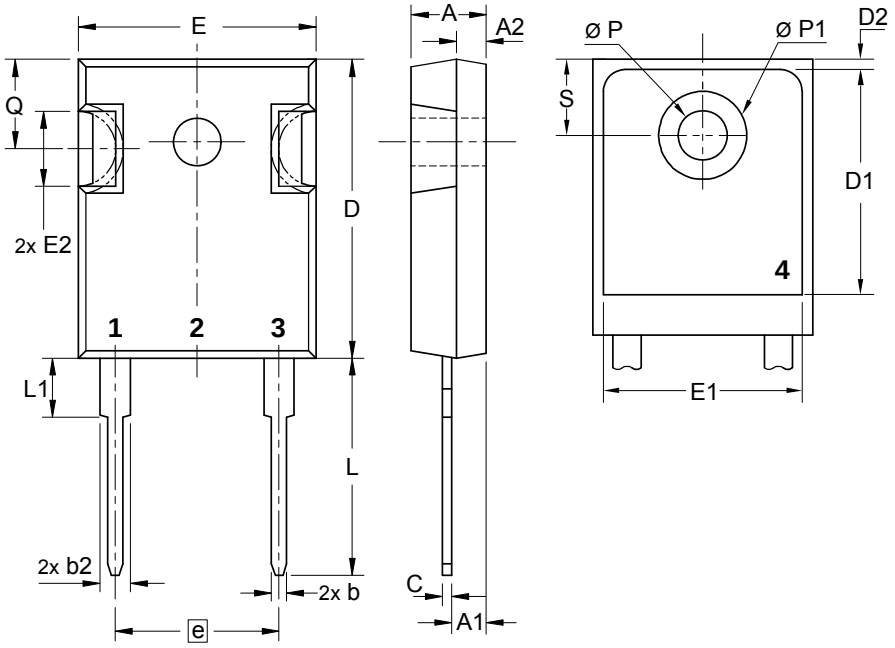
Equivalent Circuits for Simulation ** on die level* T_{VJ} = 175°C



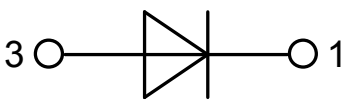
Rectifier

$V_{0\,max}$	*threshold voltage*	0.78	V
$R_{0\,max}$	*slope resistance **	2.5	mΩ

Outlines TO-247



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.430 BSC		10.92 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



Rectifier

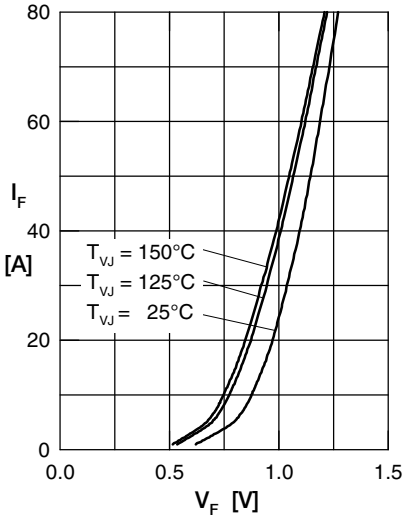


Fig. 1 Forward current versus voltage drop per diode

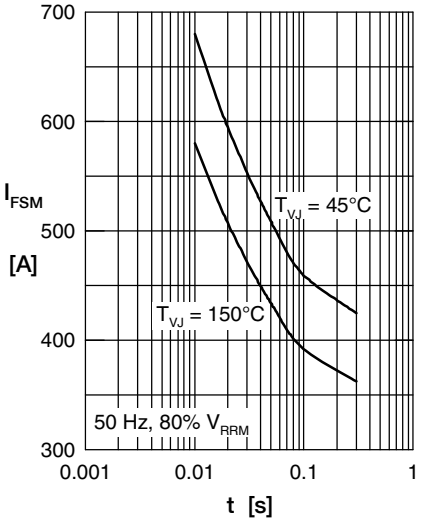


Fig. 2 Surge overload current

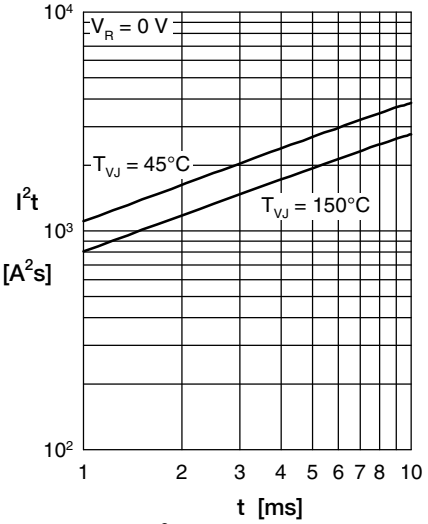


Fig. 3 I^2t versus time per diode

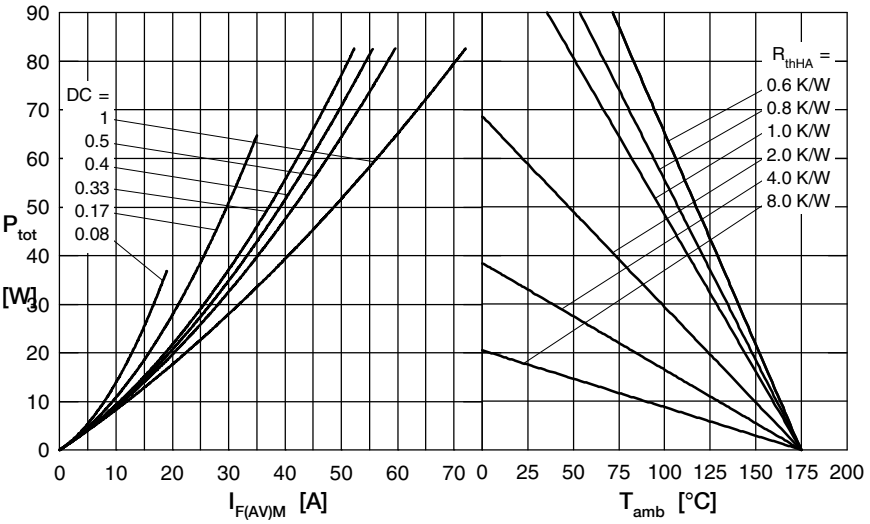


Fig. 4 Power dissipation vs. direct output current and ambient temperature

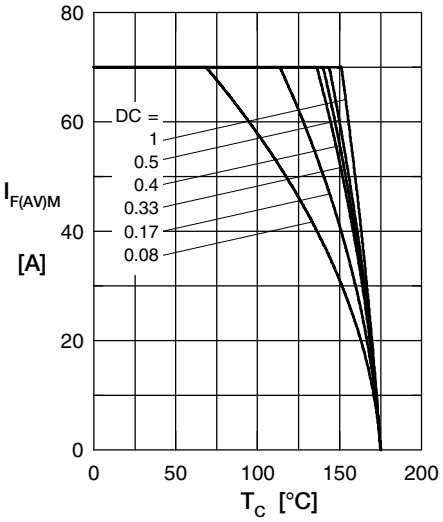


Fig. 5 Max. forward current vs. case temperature

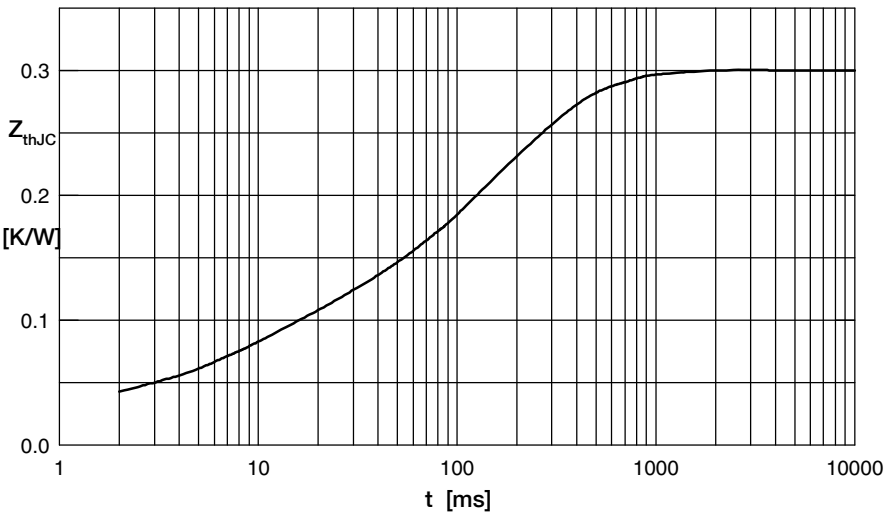


Fig. 6 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.044	0.007
2	0.027	0.0001
3	0.029	0.02
4	0.05	0.37
5	0.15	0.15